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FORMING TAPERED LOWER ELECTRODE PHASE-CHANGE MEMORIES

Abstract of the Disclosure

A phase-change memory may have a tapered lower electrode coated with an insulator. The coated, tapered electrode acts as a mask for a self-aligned trench etch to electrically separate adjacent wordlines. In some embodiments, the tapered lower electrode may be formed over a plurality of doped regions, and isotropic etching may be used to taper the electrode as well as part of the underlying doped regions.

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